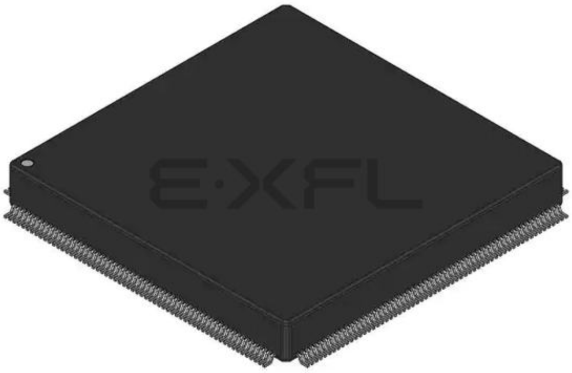


Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	360
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	189
Number of Gates	-
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	240-BFQFP
Supplier Device Package	240-PQFP (32x32)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=epf10k50sqc240-1x

- Software design support and automatic place-and-route provided by Altera's development systems for Windows-based PCs and Sun SPARCstation, and HP 9000 Series 700/800
- Flexible package options
  - Available in a variety of packages with 144 to 672 pins, including the innovative FineLine BGA™ packages (see Tables 3 and 4)
  - SameFrame™ pin-out compatibility between FLEX 10KA and FLEX 10KE devices across a range of device densities and pin counts
- Additional design entry and simulation support provided by EDIF 2 0 0 and 3 0 0 netlist files, library of parameterized modules (LPM), DesignWare components, Verilog HDL, VHDL, and other interfaces to popular EDA tools from manufacturers such as Cadence, Exemplar Logic, Mentor Graphics, OrCAD, Synopsys, Synplicity, VeriBest, and Viewlogic

Table 3. FLEX 10KE Package Options & I/O Pin Count *Notes (1), (2)*

Device	144-Pin TQFP	208-Pin PQFP	240-Pin PQFP RQFP	256-Pin FineLine BGA	356-Pin BGA	484-Pin FineLine BGA	599-Pin PGA	600-Pin BGA	672-Pin FineLine BGA
EPF10K30E	102	147		176		220			220 *(3)*
EPF10K50E	102	147	189	191		254			254 *(3)*
EPF10K50S	102	147	189	191	220	254			254 *(3)*
EPF10K100E		147	189	191	274	338			338 *(3)*
EPF10K130E			186		274	369		424	413
EPF10K200E							470	470	470
EPF10K200S			182		274	369	470	470	470

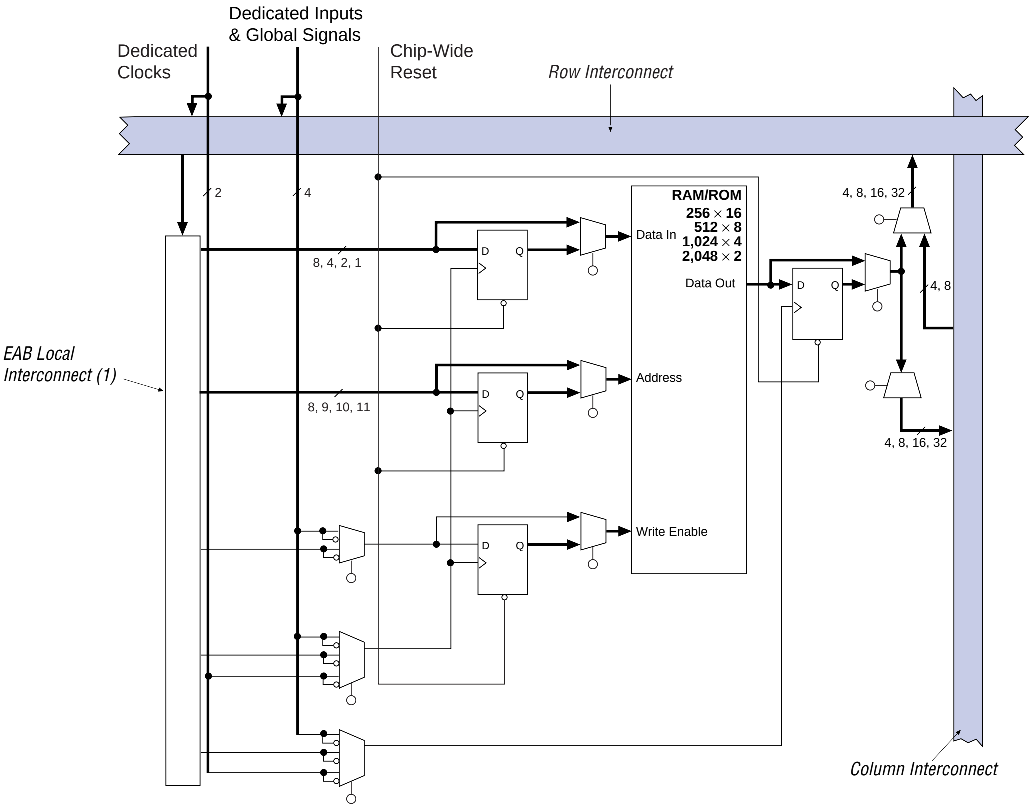
Notes:

(1) FLEX 10KE device package types include thin quad flat pack (TQFP), plastic quad flat pack (PQFP), power quad flat pack (RQFP), pin-grid array (PGA), and ball-grid array (BGA) packages.

(2) Devices in the same package are pin-compatible, although some devices have more I/O pins than others. When planning device migration, use the I/O pins that are common to all devices.

(3) This option is supported with a 484-pin FineLine BGA package. By using SameFrame pin migration, all FineLine BGA packages are pin-compatible. For example, a board can be designed to support 256-pin, 484-pin, and 672-pin FineLine BGA packages. The Altera software automatically avoids conflicting pins when future migration is set.

Figure 4. FLEX 10KE Device in Single-Port RAM Mode



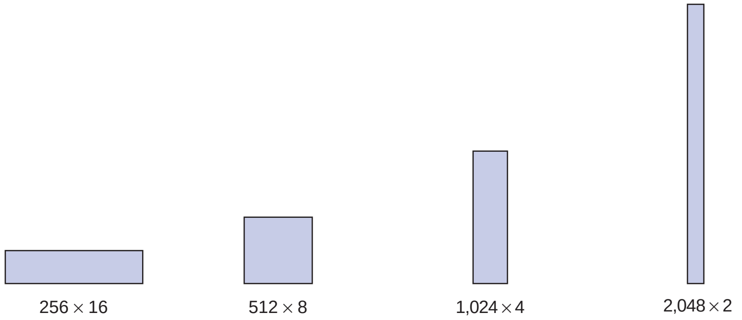
Note:

(1) EPF10K30E, EPF10K50E, and EPF10K50S devices have 88 EAB local interconnect channels; EPF10K100E, EPF10K130E, EPF10K200E, and EPF10K200S devices have 104 EAB local interconnect channels.

EABs can be used to implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the write enable signal. In contrast, the EAB's synchronous RAM generates its own write enable signal and is self-timed with respect to the input or write clock. A circuit using the EAB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

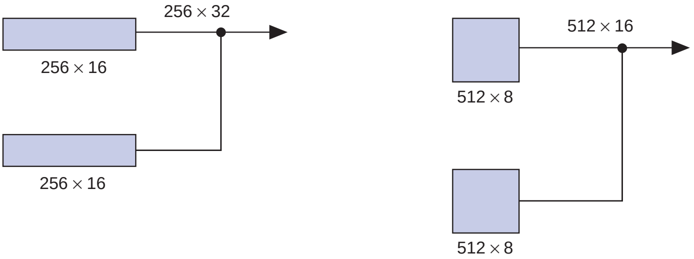
When used as RAM, each EAB can be configured in any of the following sizes: 256 × 16, 512 × 8, 1,024 × 4, or 2,048 × 2 (see Figure 5).

Figure 5. FLEX 10KE EAB Memory Configurations



Larger blocks of RAM are created by combining multiple EABs. For example, two 256 × 16 RAM blocks can be combined to form a 256 × 32 block; two 512 × 8 RAM blocks can be combined to form a 512 × 16 block (see Figure 6).

Figure 6. Examples of Combining FLEX 10KE EABs



If necessary, all EABs in a device can be cascaded to form a single RAM block. EABs can be cascaded to form RAM blocks of up to 2,048 words without impacting timing. The Altera software automatically combines EABs to meet a designer’s RAM specifications.

For improved routing, the row interconnect consists of a combination of full-length and half-length channels. The full-length channels connect to all LABs in a row; the half-length channels connect to the LABs in half of the row. The EAB can be driven by the half-length channels in the left half of the row and by the full-length channels. The EAB drives out to the full-length channels. In addition to providing a predictable, row-wide interconnect, this architecture provides increased routing resources. Two neighboring LABs can be connected using a half-row channel, thereby saving the other half of the channel for the other half of the row.

Table 7 summarizes the FastTrack Interconnect routing structure resources available in each FLEX 10KE device.

Table 7. FLEX 10KE FastTrack Interconnect Resources

Device	Rows	Channels per Row	Columns	Channels per Column
EPF10K30E	6	216	36	24
EPF10K50E EPF10K50S	10	216	36	24
EPF10K100E	12	312	52	24
EPF10K130E	16	312	52	32
EPF10K200E EPF10K200S	24	312	52	48

In addition to general-purpose I/O pins, FLEX 10KE devices have six dedicated input pins that provide low-skew signal distribution across the device. These six inputs can be used for global clock, clear, preset, and peripheral output enable and clock enable control signals. These signals are available as control signals for all LABs and IOEs in the device. The dedicated inputs can also be used as general-purpose data inputs because they can feed the local interconnect of each LAB in the device.

Figure 14 shows the interconnection of adjacent LABs and EABs, with row, column, and local interconnects, as well as the associated cascade and carry chains. Each LAB is labeled according to its location: a letter represents the row and a number represents the column. For example, LAB B3 is in row B, column 3.

ClockLock & ClockBoost Features

To support high-speed designs, FLEX 10KE devices offer optional ClockLock and ClockBoost circuitry containing a phase-locked loop (PLL) used to increase design speed and reduce resource usage. The ClockLock circuitry uses a synchronizing PLL that reduces the clock delay and skew within a device. This reduction minimizes clock-to-output and setup times while maintaining zero hold times. The ClockBoost circuitry, which provides a clock multiplier, allows the designer to enhance device area efficiency by resource sharing within the device. The ClockBoost feature allows the designer to distribute a low-speed clock and multiply that clock on-device. Combined, the ClockLock and ClockBoost features provide significant improvements in system performance and bandwidth.

All FLEX 10KE devices, except EPF10K50E and EPF10K200E devices, support ClockLock and ClockBoost circuitry. EPF10K50S and EPF10K200S devices support this circuitry. Devices that support ClockLock and ClockBoost circuitry are distinguished with an “X” suffix in the ordering code; for instance, the EPF10K200SFC672-1X device supports this circuit.

The ClockLock and ClockBoost features in FLEX 10KE devices are enabled through the Altera software. External devices are not required to use these features. The output of the ClockLock and ClockBoost circuits is not available at any of the device pins.

The ClockLock and ClockBoost circuitry locks onto the rising edge of the incoming clock. The circuit output can drive the clock inputs of registers only; the generated clock cannot be gated or inverted.

The dedicated clock pin (`GCLK1`) supplies the clock to the ClockLock and ClockBoost circuitry. When the dedicated clock pin is driving the ClockLock or ClockBoost circuitry, it cannot drive elsewhere in the device.

For designs that require both a multiplied and non-multiplied clock, the clock trace on the board can be connected to the `GCLK1` pin. In the Altera software, the `GCLK1` pin can feed both the ClockLock and ClockBoost circuitry in the FLEX 10KE device. However, when both circuits are used, the other clock pin cannot be used.

Table 17. 32-Bit IDCODE for FLEX 10KE Devices *Note (1)*

Device	IDCODE (32 Bits)			
	Version (4 Bits)	**Part Number (16 Bits)**	**Manufacturer's Identity (11 Bits)**	**1 (1 Bit)** *(2)*
EPF10K30E	`0001`	`0001 0000 0011 0000`	`00001101110`	`1`
EPF10K50E EPF10K50S	`0001`	`0001 0000 0101 0000`	`00001101110`	`1`
EPF10K100E	`0010`	`0000 0001 0000 0000`	`00001101110`	`1`
EPF10K130E	`0001`	`0000 0001 0011 0000`	`00001101110`	`1`
EPF10K200E EPF10K200S	`0001`	`0000 0010 0000 0000`	`00001101110`	`1`

Notes:

(1) The most significant bit (MSB) is on the left.

(2) The least significant bit (LSB) for all JTAG IDCODEs is `1`.

FLEX 10KE devices include weak pull-up resistors on the JTAG pins.

For more information, see the following documents:

- *Application Note 39 (IEEE Std. 1149.1 (JTAG) Boundary-Scan Testing in Altera Devices)*
- *BitBlaster Serial Download Cable Data Sheet*
- *ByteBlasterMV Parallel Port Download Cable Data Sheet*
- *Jam Programming & Test Language Specification*

Figure 25. FLEX 10KE Device LE Timing Model

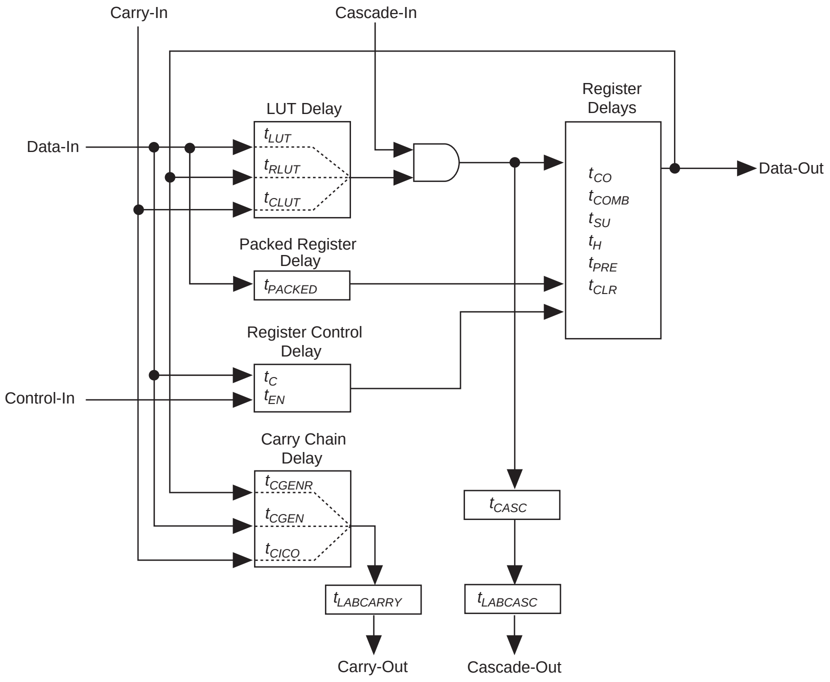


Figure 26. FLEX 10KE Device IOE Timing Model

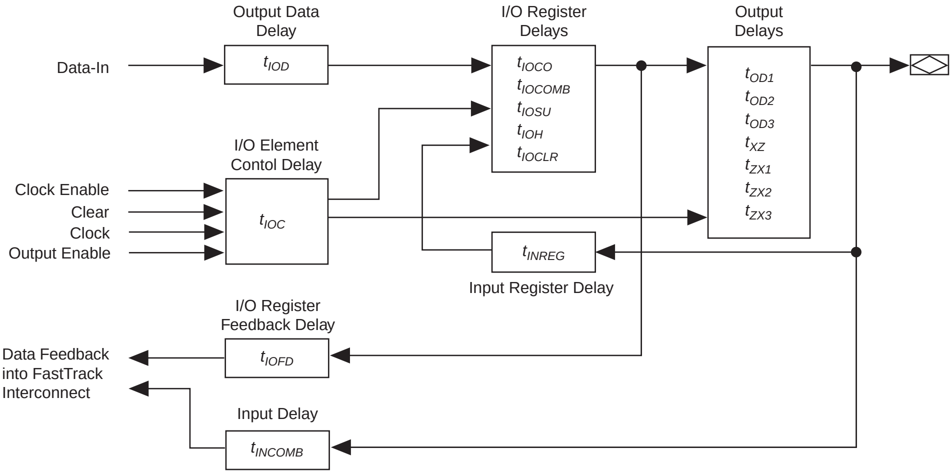


Figure 27. FLEX 10KE Device EAB Timing Model

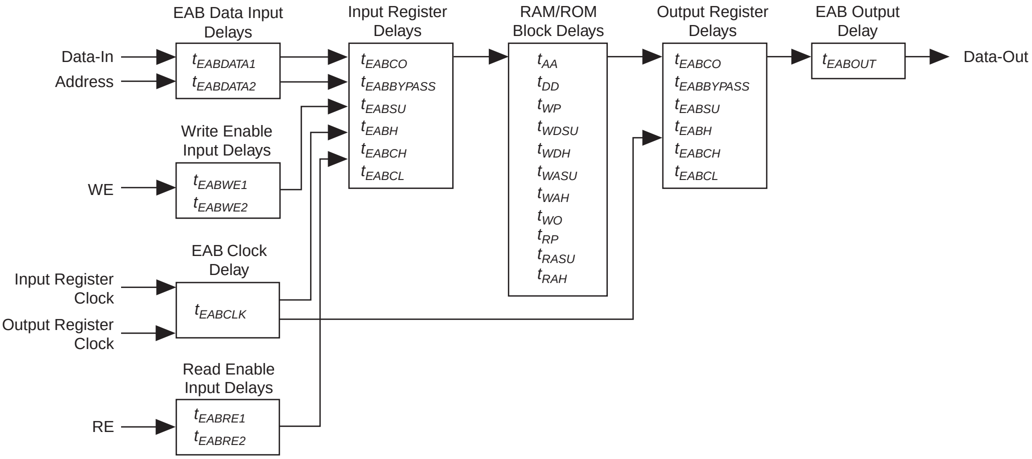


Table 26. EAB Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
$t_{EABDATA1}$	Data or address delay to EAB for combinatorial input	
$t_{EABDATA2}$	Data or address delay to EAB for registered input	
t_{EABWE1}	Write enable delay to EAB for combinatorial input	
t_{EABWE2}	Write enable delay to EAB for registered input	
t_{EABRE1}	Read enable delay to EAB for combinatorial input	
t_{EABRE2}	Read enable delay to EAB for registered input	
t_{EABCLK}	EAB register clock delay	
t_{EABCO}	EAB register clock-to-output delay	
$t_{EABBYPASS}$	Bypass register delay	
t_{EABSU}	EAB register setup time before clock	
t_{EABH}	EAB register hold time after clock	
t_{EABCLR}	EAB register asynchronous clear time to output delay	
t_{AA}	Address access delay (including the read enable to output delay)	
t_{WP}	Write pulse width	
t_{RP}	Read pulse width	
t_{WDSU}	Data setup time before falling edge of write pulse	*(5)*
t_{WDH}	Data hold time after falling edge of write pulse	*(5)*
t_{WASU}	Address setup time before rising edge of write pulse	*(5)*
t_{WAH}	Address hold time after falling edge of write pulse	*(5)*
t_{RASU}	Address setup time with respect to the falling edge of the read enable	
t_{RAH}	Address hold time with respect to the falling edge of the read enable	
t_{WO}	Write enable to data output valid delay	
t_{DD}	Data-in to data-out valid delay	
t_{EABOUT}	Data-out delay	
t_{EABCH}	Clock high time	
t_{EABCL}	Clock low time	

Table 28. Interconnect Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
$t_{DIN2IOE}$	Delay from dedicated input pin to IOE control input	(7)
t_{DIN2LE}	Delay from dedicated input pin to LE or EAB control input	(7)
$t_{DCLK2IOE}$	Delay from dedicated clock pin to IOE clock	(7)
$t_{DCLK2LE}$	Delay from dedicated clock pin to LE or EAB clock	(7)
$t_{DIN2DATA}$	Delay from dedicated input or clock to LE or EAB data	(7)
$t_{SAMELAB}$	Routing delay for an LE driving another LE in the same LAB	
$t_{SAMEROW}$	Routing delay for a row IOE, LE, or EAB driving a row IOE, LE, or EAB in the same row	(7)
$t_{SAMECOLUMN}$	Routing delay for an LE driving an IOE in the same column	(7)
$t_{DIFFROW}$	Routing delay for a column IOE, LE, or EAB driving an LE or EAB in a different row	(7)
$t_{TWOROWS}$	Routing delay for a row IOE or EAB driving an LE or EAB in a different row	(7)
$t_{LEPERIPH}$	Routing delay for an LE driving a control signal of an IOE via the peripheral control bus	(7)
$t_{LABCARRY}$	Routing delay for the carry-out signal of an LE driving the carry-in signal of a different LE in a different LAB	
$t_{LABCASC}$	Routing delay for the cascade-out signal of an LE driving the cascade-in signal of a different LE in a different LAB	

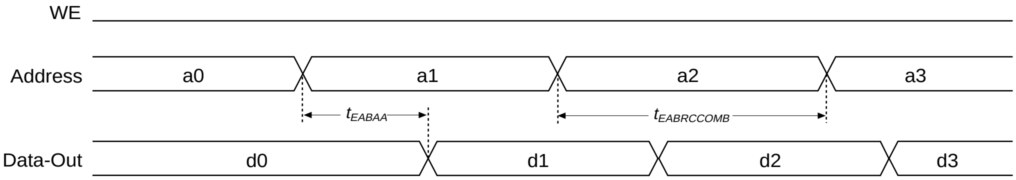
Table 29. External Timing Parameters

Symbol	Parameter	Conditions
t_{DRR}	Register-to-register delay via four LEs, three row interconnects, and four local interconnects	(8)
t_{INSU}	Setup time with global clock at IOE register	(9)
t_{INH}	Hold time with global clock at IOE register	(9)
t_{OUTCO}	Clock-to-output delay with global clock at IOE register	(9)
t_{PCISU}	Setup time with global clock for registers used in PCI designs	(9),(10)
t_{PCIH}	Hold time with global clock for registers used in PCI designs	(9),(10)
t_{PCICO}	Clock-to-output delay with global clock for registers used in PCI designs	(9),(10)

Figures 29 and 30 show the asynchronous and synchronous timing waveforms, respectively, or the EAB macroparameters in Tables 26 and 27.

Figure 29. EAB Asynchronous Timing Waveforms

EAB Asynchronous Read



EAB Asynchronous Write

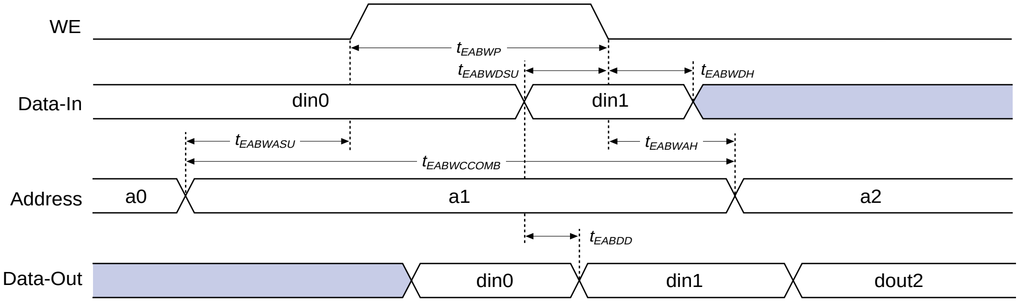


Table 33. EPF10K30E Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
$t_{EABDATA1}$		1.7		2.0		2.3	ns
$t_{EABDATA1}$		0.6		0.7		0.8	ns
t_{EABWE1}		1.1		1.3		1.4	ns
t_{EABWE2}		0.4		0.4		0.5	ns
t_{EABRE1}		0.8		0.9		1.0	ns
t_{EABRE2}		0.4		0.4		0.5	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.3		0.3		0.4	ns
$t_{EABBYPASS}$		0.5		0.6		0.7	ns
t_{EABSU}	0.9		1.0		1.2		ns
t_{EABH}	0.4		0.4		0.5		ns
t_{EABCLR}	0.3		0.3		0.3		ns
t_{AA}		3.2		3.8		4.4	ns
t_{WP}	2.5		2.9		3.3		ns
t_{RP}	0.9		1.1		1.2		ns
t_{WDSU}	0.9		1.0		1.1		ns
t_{WDH}	0.1		0.1		0.1		ns
t_{WASU}	1.7		2.0		2.3		ns
t_{WAH}	1.8		2.1		2.4		ns
t_{RASU}	3.1		3.7		4.2		ns
t_{RAH}	0.2		0.2		0.2		ns
t_{WO}		2.5		2.9		3.3	ns
t_{DD}		2.5		2.9		3.3	ns
t_{EABOUT}		0.5		0.6		0.7	ns
t_{EABCH}	1.5		2.0		2.3		ns
t_{EABCL}	2.5		2.9		3.3		ns

Table 56. EPF10K130E Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		2.8		3.5		4.4	ns
t_{DIN2LE}		0.7		1.2		1.6	ns
$t_{DIN2DATA}$		1.6		1.9		2.2	ns
$t_{DCLK2IOE}$		1.6		2.1		2.7	ns
$t_{DCLK2LE}$		0.7		1.2		1.6	ns
$t_{SAMELAB}$		0.1		0.2		0.2	ns
$t_{SAMEROW}$		1.9		3.4		5.1	ns
$t_{SAMECOLUMN}$		0.9		2.6		4.4	ns
$t_{DIFFROW}$		2.8		6.0		9.5	ns
$t_{TWOROWS}$		4.7		9.4		14.6	ns
$t_{LEPERIPH}$		3.1		4.7		6.9	ns
$t_{LABCARRY}$		0.6		0.8		1.0	ns
$t_{LABCASC}$		0.9		1.2		1.6	ns

Table 57. EPF10K130E External Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		9.0		12.0		16.0	ns
t_{INSU} *(3)*	1.9		2.1		3.0		ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.0	2.0	7.0	2.0	9.2	ns
t_{INSU} *(4)*	0.9		1.1		–		ns
t_{INH} *(4)*	0.0		0.0		–		ns
t_{OUTCO} *(4)*	0.5	4.0	0.5	6.0	–	–	ns
t_{PCISU}	3.0		6.2		–		ns
t_{PCIH}	0.0		0.0		–		ns
t_{PCICO}	2.0	6.0	2.0	6.9	–	–	ns

Table 64. EPF10K200E External Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		10.0		12.0		16.0	ns
t_{INSU}	2.8		3.4		4.4		ns
t_{INH}	0.0		0.0		0.0		ns
t_{OUTCO}	2.0	4.5	2.0	5.3	2.0	7.8	ns
t_{PCISU}	3.0		6.2		-		ns
t_{PCIH}	0.0		0.0		-		ns
t_{PCICO}	2.0	6.0	2.0	8.9	-	-	ns

Table 65. EPF10K200E External Bidirectional Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	3.0		4.0		5.5		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	4.5	2.0	5.3	2.0	7.8	ns
$t_{XZBIDIR}$		8.1		9.5		13.0	ns
$t_{ZXBIDIR}$		8.1		9.5		13.0	ns

Notes to tables:

(1) All timing parameters are described in Tables 24 through 30 in this data sheet.

(2) These parameters are specified by characterization.

Tables 66 through 79 show EPF10K50S and EPF10K200S device external timing parameters.

Table 66. EPF10K50S Device LE Timing Microparameters (Part 1 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.6		0.8		1.1	ns
t_{CLUT}		0.5		0.6		0.8	ns
t_{RLUT}		0.6		0.7		0.9	ns
t_{PACKED}		0.2		0.3		0.4	ns
t_{EN}		0.6		0.7		0.9	ns
t_{CICO}		0.1		0.1		0.1	ns
t_{CGEN}		0.4		0.5		0.6	ns

Table 69. EPF10K50S Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		3.7		5.2		7.0	ns
$t_{EABRCCOMB}$	3.7		5.2		7.0		ns
$t_{EABRCREG}$	3.5		4.9		6.6		ns
t_{EABWP}	2.0		2.8		3.8		ns
$t_{EABWCCOMB}$	4.5		6.3		8.6		ns
$t_{EABWCREG}$	5.6		7.8		10.6		ns
t_{EABDD}		3.8		5.3		7.2	ns
$t_{EABDATACO}$		0.8		1.1		1.5	ns
$t_{EABDATASU}$	1.1		1.6		2.1		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	0.7		1.0		1.3		ns
t_{EABWEH}	0.4		0.6		0.8		ns
$t_{EABWDSU}$	1.2		1.7		2.2		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	1.6		2.3		3.0		ns
t_{EABWAH}	0.9		1.2		1.8		ns
t_{EABWO}		3.1		4.3		5.9	ns

Table 70. EPF10K50S Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		3.1		3.7		4.6	ns
t_{DIN2LE}		1.7		2.1		2.7	ns
$t_{DIN2DATA}$		2.7		3.1		5.1	ns
$t_{DCLK2IOE}$		1.6		1.9		2.6	ns
$t_{DCLK2LE}$		1.7		2.1		2.7	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		1.5		1.7		2.4	ns
$t_{SAMECOLUMN}$		1.0		1.3		2.1	ns
$t_{DIFFROW}$		2.5		3.0		4.5	ns
$t_{TWOROWS}$		4.0		4.7		6.9	ns
$t_{LEPERIPH}$		2.6		2.9		3.4	ns
$t_{LABCARRY}$		0.1		0.2		0.2	ns
$t_{LABCASC}$		0.8		1.0		1.3	ns

Table 74. EPF10K200S Device IOE Timing Microparameters (Part 2 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ZX2}		4.5		4.8		6.6	ns
t_{ZX3}		6.6		7.6		10.1	ns
t_{INREG}		3.7		5.7		7.7	ns
t_{IOFD}		1.8		3.4		4.0	ns
t_{INCOMB}		1.8		3.4		4.0	ns

Table 75. EPF10K200S Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.8		2.4		3.2	ns
$t_{EABDATA1}$		0.4		0.5		0.6	ns
t_{EABWE1}		1.1		1.7		2.3	ns
t_{EABWE2}		0.0		0.0		0.0	ns
t_{EABRE1}		0		0		0	ns
t_{EABRE2}		0.4		0.5		0.6	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.8		0.9		1.2	ns
$t_{EABBYPASS}$		0.0		0.1		0.1	ns
t_{EABSU}	0.7		1.1		1.5		ns
t_{EABH}	0.4		0.5		0.6		ns
t_{EABCLR}	0.8		0.9		1.2		ns
t_{AA}		2.1		3.7		4.9	ns
t_{WP}	2.1		4.0		5.3		ns
t_{RP}	1.1		1.1		1.5		ns
t_{WDSU}	0.5		1.1		1.5		ns
t_{WDH}	0.1		0.1		0.1		ns
t_{WASU}	1.1		1.6		2.1		ns
t_{WAH}	1.6		2.5		3.3		ns
t_{RASU}	1.6		2.6		3.5		ns
t_{RAH}	0.1		0.1		0.2		ns
t_{WO}		2.0		2.4		3.2	ns
t_{DD}		2.0		2.4		3.2	ns
t_{EABOUT}		0.0		0.1		0.1	ns
t_{EABCH}	1.5		2.0		2.5		ns
t_{EABCL}	2.1		2.8		3.8		ns

Table 76. EPF10K200S Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		3.9		6.4		8.4	ns
$t_{EABRCOMB}$	3.9		6.4		8.4		ns
$t_{EABRCREG}$	3.6		5.7		7.6		ns
t_{EABWP}	2.1		4.0		5.3		ns
$t_{EABWCOMB}$	4.8		8.1		10.7		ns
$t_{EABWCREG}$	5.4		8.0		10.6		ns
t_{EABDD}		3.8		5.1		6.7	ns
$t_{EABDATACO}$		0.8		1.0		1.3	ns
$t_{EABDATASU}$	1.1		1.6		2.1		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	0.7		1.1		1.5		ns
t_{EABWEH}	0.4		0.5		0.6		ns
$t_{EABWDSU}$	1.2		1.8		2.4		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	1.9		3.6		4.7		ns
t_{EABWAH}	0.8		0.5		0.7		ns
t_{EABWO}		3.1		4.4		5.8	ns

Table 77. EPF10K200S Device Interconnect Timing Microparameters (Part 1 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		4.4		4.8		5.5	ns
t_{DIN2LE}		0.6		0.6		0.9	ns
$t_{DIN2DATA}$		1.8		2.1		2.8	ns
$t_{DCLK2IOE}$		1.7		2.0		2.8	ns
$t_{DCLK2LE}$		0.6		0.6		0.9	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		3.0		4.6		5.7	ns
$t_{SAMECOLUMN}$		3.5		4.9		6.4	ns
$t_{DIFFROW}$		6.5		9.5		12.1	ns
$t_{TWOROWS}$		9.5		14.1		17.8	ns
$t_{LEPERIPH}$		5.5		6.2		7.2	ns
$t_{LABCARRY}$		0.3		0.1		0.2	ns

To better reflect actual designs, the power model (and the constant K in the power calculation equations) for continuous interconnect FLEX devices assumes that LEs drive FastTrack Interconnect channels. In contrast, the power model of segmented FPGAs assumes that all LEs drive only one short interconnect segment. This assumption may lead to inaccurate results when compared to measured power consumption for actual designs in segmented FPGAs.

Figure 31 shows the relationship between the current and operating frequency of FLEX 10KE devices.

Figure 31. FLEX 10KE $I_{CCACTIVE}$ vs. Operating Frequency (Part 1 of 2)

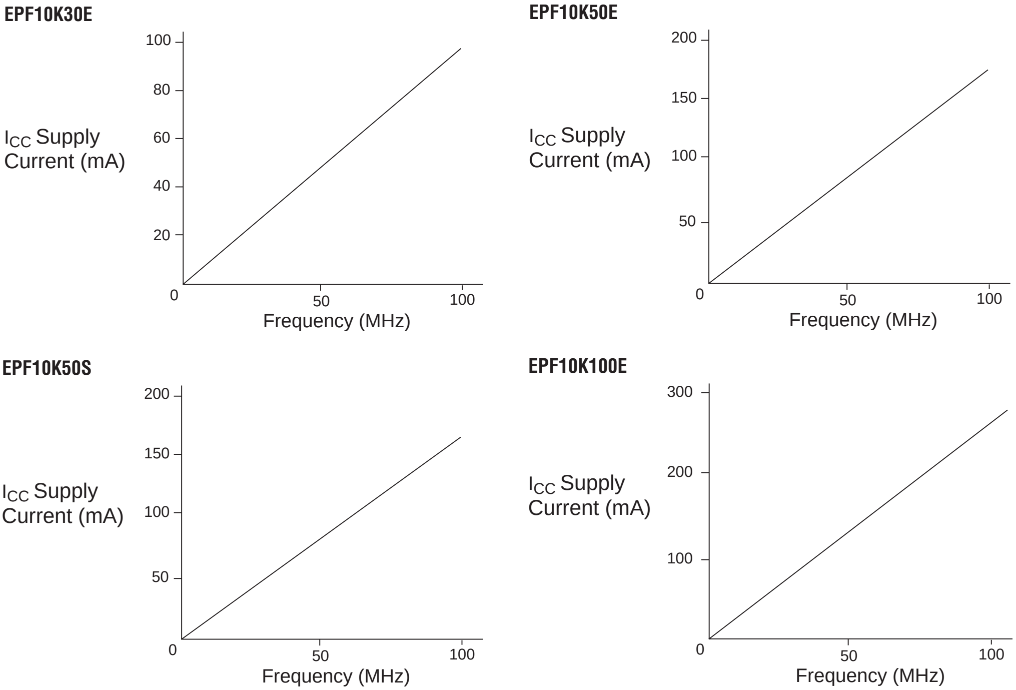
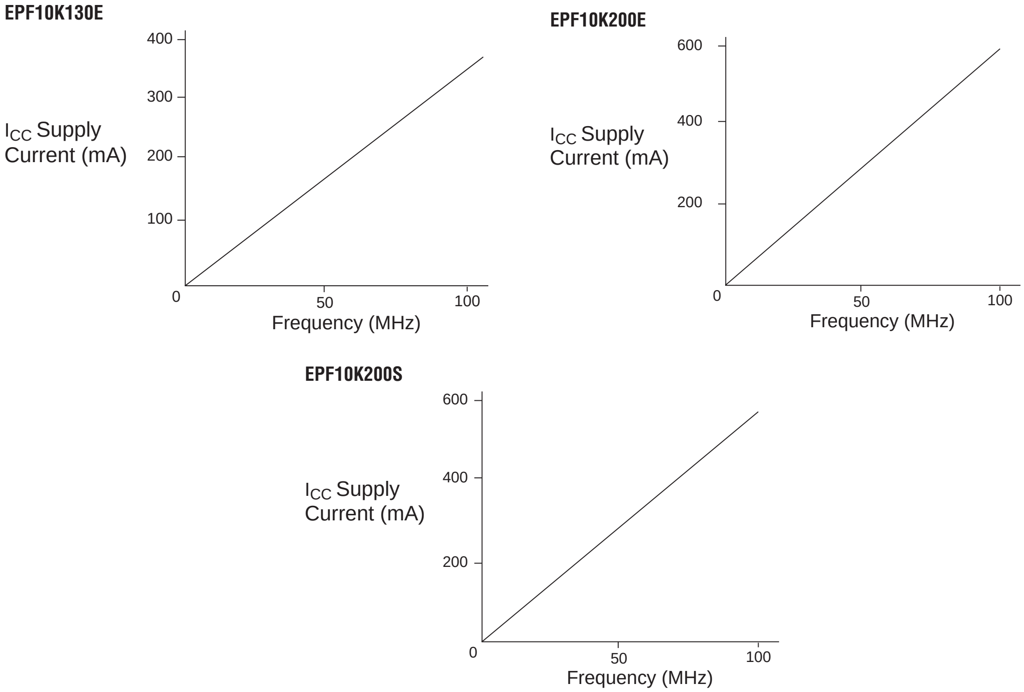


Figure 31. FLEX 10KE $I_{CCACTIVE}$ vs. Operating Frequency (Part 2 of 2)



Configuration & Operation

The FLEX 10KE architecture supports several configuration schemes. This section summarizes the device operating modes and available device configuration schemes.

Operating Modes

The FLEX 10KE architecture uses SRAM configuration elements that require configuration data to be loaded every time the circuit powers up. The process of physically loading the SRAM data into the device is called *configuration*. Before configuration, as V_{CC} rises, the device initiates a Power-On Reset (POR). This POR event clears the device and prepares it for configuration. The FLEX 10KE POR time does not exceed 50 µs.

When configuring with a configuration device, refer to the respective configuration device data sheet for POR timing information.

Device Pin-Outs

See the Altera web site (**http://www.altera.com**) or the Altera Digital Library for pin-out information.

Revision History

The information contained in the *FLEX 10KE Embedded Programmable Logic Data Sheet* version 2.5 supersedes information published in previous versions.

Version 2.5

The following changes were made to the *FLEX 10KE Embedded Programmable Logic Data Sheet* version 2.5:

- *Note (1)* added to Figure 23.
- Text added to "I/O Element" section on page 34.
- Updated Table 22.

Version 2.4

The following changes were made to the *FLEX 10KE Embedded Programmable Logic Data Sheet* version 2.4: updated text on page 34 and page 63.